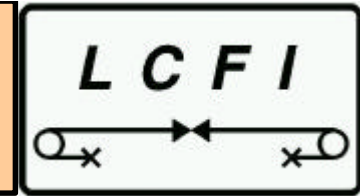


WP-6 – Thin-Ladder R&D



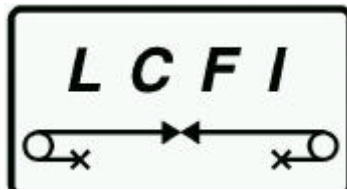
- ◆ **Objective – to design a CCD support structure with the following properties:**
 - ◆ **Complete assembly must have ultra-low mass ($\ll 0.4\% X_0$ – SLD VXD3)**
 - ◆ **CCD adopting a non-planar 3-d profile is tolerable at ~few tens of micron level, but must be repeatable to ~micron level with temperature cycling ($\sim \pm 50^\circ\text{C}$)**
 - ◆ **CCD must be mechanically stable at ~micron level wrt small temperature excursions ($\sim \pm 5^\circ\text{C}$) – no “metastable” behaviour**
 - ◆ **CCD capable of planarisation at each end for bump-bonding of Readout Chip**
 - ◆ **Overall assembly sufficiently robust for safe handling (*with appropriate jigs*)**
 - ◆ **Structure must allow use of evaporative gas-cooling (*low-impedance to gas-flow*)**



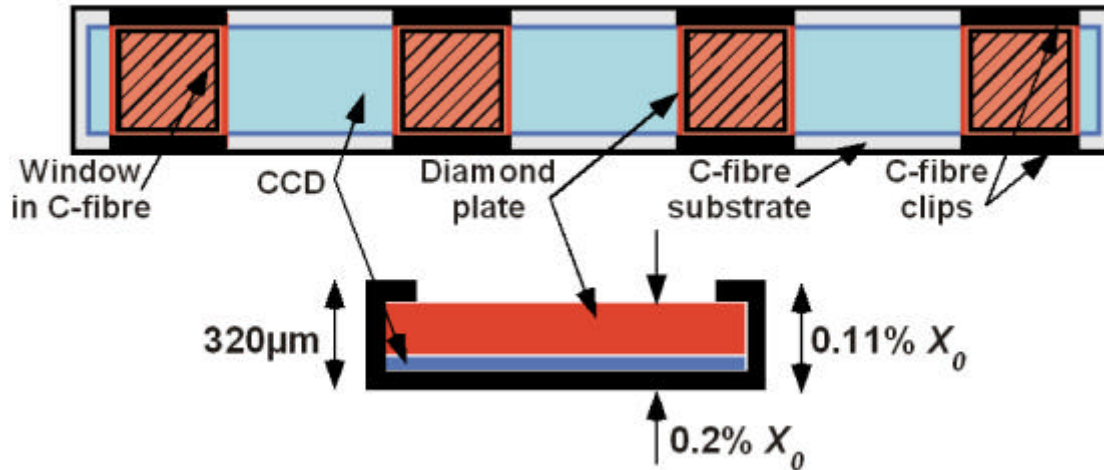
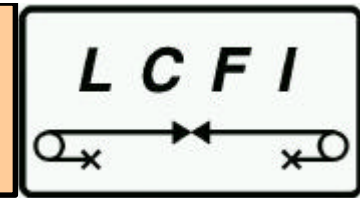
- ◆ Three main approaches:
- ◆ In order of diminishing X/X_0 –
 - ◆ Fully-supported CCDs – thinned Si bonded to 3-d rigid substrate (e.g. Be)
 - ◆ Semi-supported CCDs – thinned Si attached to planar substrate, with rigidity achieved by tensioning substrate in z
 - ◆ Unsupported CCDs – thinned Si with no substrate, rigidity of effective membrane achieved by tensioning Si in z
- ◆ Only the last two have been studied so far
- ◆ Unsupported Si option very attractive from low-mass aspect, *but ...*
 - ◆ CCD processing → severe differential thermal contraction effects → curling
 - ◆ Longitudinal curling removed by tensioning in z, but lateral curling → instability



- ◆ Unsupported Si option very attractive from low-mass aspect, *but ...*
 - ◆ CCD processing → severe differential thermal contraction effects → curling
 - ◆ Longitudinal curling removed by tensioning in z, but lateral curling → instability
 - ◆ Problem of joining B2–B5 ladders at $z = 0$ (*reliability of narrow adhesive bond*)
 - ◆ Handling (*bump-bonding, testing, assembly, ...*) of ladders could be a potential (*probable?*) nightmare → low yield
- ◆ Lateral curling could be reduced by cross-bracing (*Si, ceramic, ... ?*)
 - ◆ Increase in X/X_0 in several local regions
- ◆ Semi-supported Si option currently being studied
 - ◆ Several possible techniques and different materials – all have *pros and cons!*
 - ◆ Simulation very important to narrow down options – much faster than making physical models



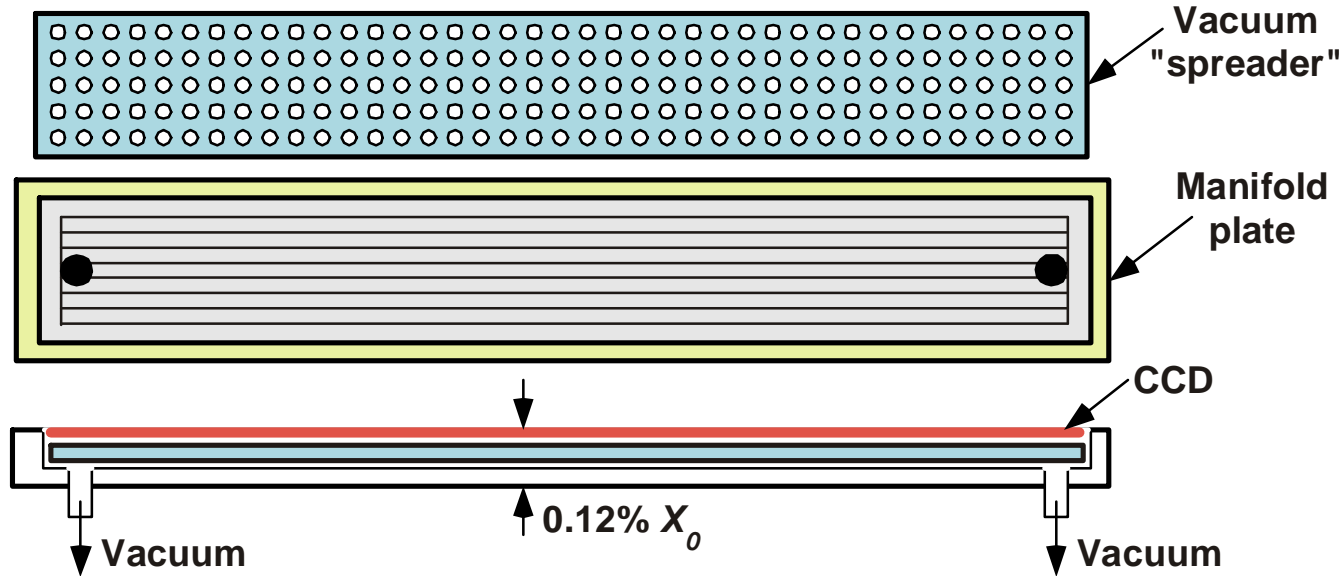
C-fibre substrate with CVD diamond retainers



- ◆ CCD free to slide between substrate and diamond plates
- ◆ Plates + substrate planarise CCD
- ◆ 200µm CVD diamond – 0.16% X_0
- ◆ 50µm C-fibre – 0.02% X_0
- ◆ Min layer thickness – 0.04% X_0

◆ Potential problems:

- ◆ Layer thickness increases by factor ~5 (0.04% X_0 – 0.2% X_0) for ~50% of active area
- ◆ Tolerances on plate-substrate gap – thermal contraction effects
- ◆ Longitudinal borders → extra material in ladder overlap regions
- ◆ Mechanical damage to CCD gate/bus structures
- ◆ Possible effect on gate capacitance?
- ◆ Lateral curling of CCD in free regions – adhesive still needed?



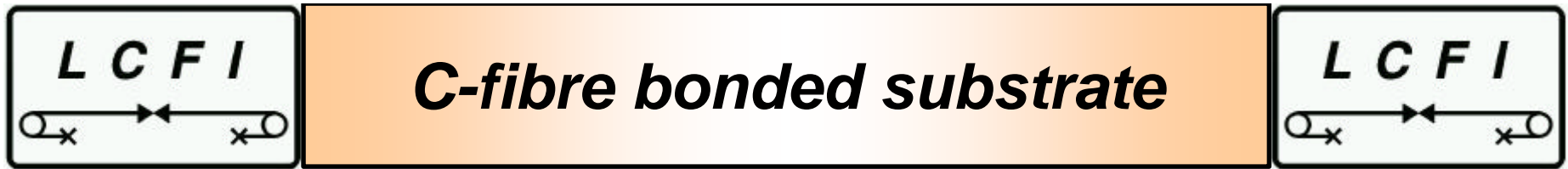
◆ C-fibre (Be) – 100µm thick manifold, 200µm thick vacuum “spreader”

◆ CCD pulled flat by applied vacuum, via “spreader”

◆ Uniform low layer thickness –
 0.12% X_0 (C-fibre)
 0.09% X_0 (Be)

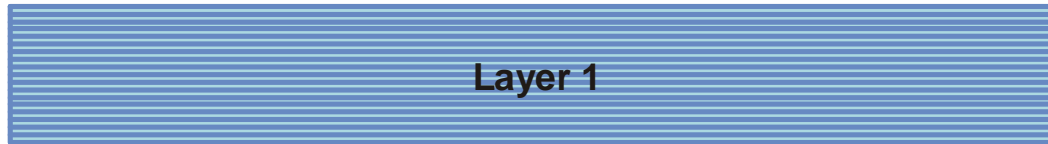
◆ **Potential problems:**

- ◆ “Spreader” (=substrate!) could distort from planar with stress-induced matrix of holes
- ◆ Overlap of in-barrel ladders complicated due to longitudinal borders of manifold plate and orthogonal vacuum pipes and introduce more material in overlap regions
- ◆ Repeatability of CCD position with vacuum cycling
- ◆ Handling – bump-bonding Readout Chip, vacuum retention and transfer, assembly, ...
- ◆ Loss of vacuum MUST produce a fail-safe state – retaining clamps may be needed



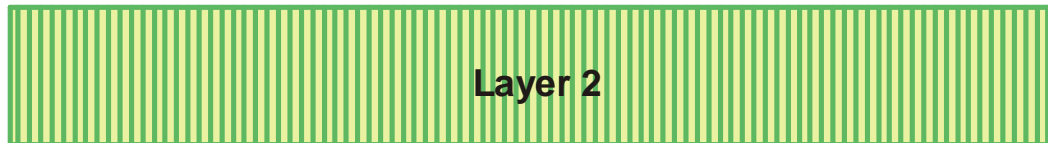
◆ C-fibre diameter → 10µm

◆ Sheet thickness → 60µm



◆ 3 orthogonal layers → ~200µm

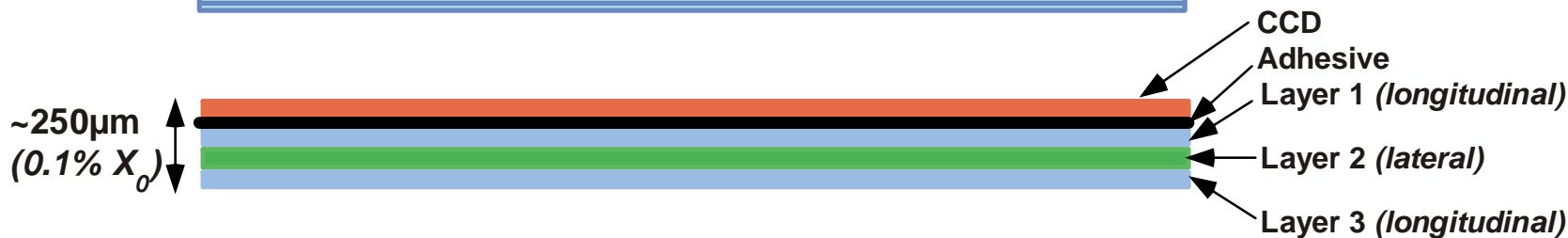
◆ C-fibre CTE < Si CTE, so Si in tension along ladder @ -50 °C



◆ CTE tuneable to 0 in principle



◆ Further external tensioning can be used to remove any unbalanced longitudinal bow

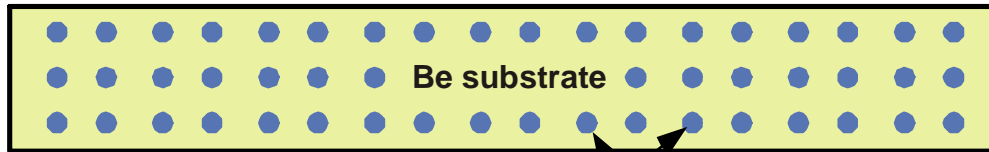


◆ **Potential problems:**

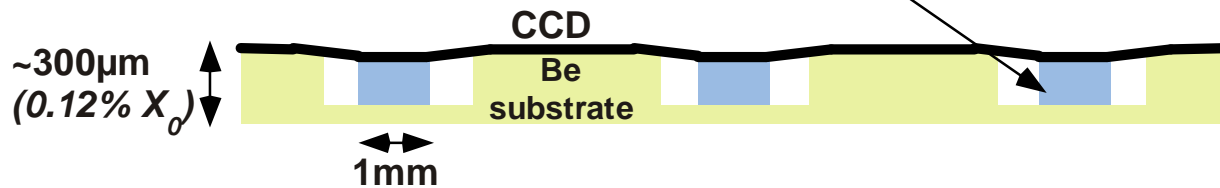
◆ Early test samples showed very poor surface quality (*large diameter C-fibres?*)

◆ Much more study needed – many new variants now appearing – but difficult to simulate

LCFI **Floating Si on Be substrate** **LCFI**



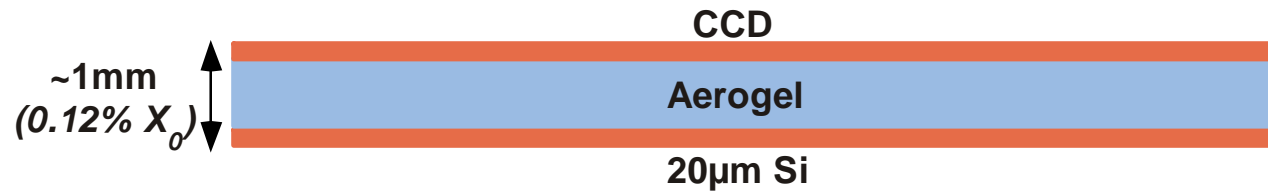
Recessed NuSil adhesive pads



- ◆ CCD bonded with compliant adhesive pads (e.g. NuSil) to thin (250µm) Be substrate
- ◆ On cooling, differential thermal contraction → Si into tension → NuSil columns tilt
- ◆ Layer thickness → 0.12% X_0
- ◆ 1mm diameter NuSil columns inside 2mm diameter wells 200µm deep in Be substrate
- ◆ On cooling, NuSil contracts more than Be → pulls Si down on to Be surface

◆ **Potential problems:**

- ◆ CCD surface may become dimpled – magnitude of effect and repeatability unknown
- ◆ May need very fine pitch of NuSil pad matrix → difficult assembly procedure, weakened substrate, complex non-uniform layer thickness (X/X_0), ...
- ◆ Simulation crucial – early results from ANSYS look promising



- ◆ 3-layer sandwich made from ~1mm Aerogel between thinned ($20\mu\text{m}$?) CCD and $20\mu\text{m}$ Si balancing membrane
- ◆ Silica Aerogel chemically bonds to Si (*CCD and compensating membrane*)
- ◆ Si has higher CTE so on cooling it is put into tension – Aerogel in compression
- ◆ **Potential problems:**
 - ◆ If attachment needs to be done at time of Si processing – adds complexity
 - ◆ What happens at ends of ladder – bump-bonding of Readout Chip?
 - ◆ B2 – B5 ladders have pairs of CCDs – is Aerogel strength alone sufficient in the inter-CCD gap region (*tensioning impossible – Aerogel weak in tension*)?
 - ◆ Needs much more study – early ideas only



◆ **Conclusions**

- ◆ **Several interesting and ingenious mechanical ideas**
- ◆ **Some novel materials now being investigated**
- ◆ **Making physical test structures takes time, so simulation is vital for guidance → avoid time-consuming dead-ends**
- ◆ **Many potential show-stoppers – differential CTE effects, X_0 , bump-bonding of Readout Chip, handling**